





N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max
40V	42mΩ @ V _{GS} = 10V	4.6A
	52mΩ @ V _{GS} = 4.5V	4.1A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMN4035LQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

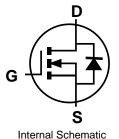
- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

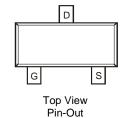
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 <a>3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



Top View





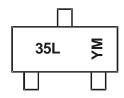
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN4035LQ-7	SOT23	3000/Tape & Reel
DMN4035LQ-13	SOT23	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



35L = Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

_	Bate Code Hoy												
	Year	2019	20	20	2021	2022	20	23	2024	2025	20	26	2027
	Code	G	ŀ	1	I	J	ŀ	<	L	M	ı	N	0
Ī	Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
ı	Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	40	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 6) V _{GS} = 10V	lo	4.6 3.7	А		
Maximum Body Diode Forward Current (Note 6)		Is	1.5	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	25	Α		
Pulsed Source Current (10µs Pulse, Duty Cycle = 19	%)		Ism	25	Α

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Power Dissipation (Note 5)		PD	0.72	W
Thermal Resistance, Junction to Ambient (Note 5) Steady State		Reja	171	°C/W
Power Dissipation (Note 6)		PD	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	93	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	•				1	1	
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	V _{GS} = 0V, I _D = 250μA	
Zero Gate Voltage Drain Current	IDSS		_	1	μΑ	V _{DS} = 40V, V _{GS} = 0V	
Gate-Source Leakage	Igss		_	±100	nA	Vgs = ±20V, Vps = 0V	
ON CHARACTERISTICS (Note 7)	•			•	•		
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	D	-	30	42	mΩ	V _G S = 10V, I _D = 4.3A	
Static Diain-Source On-Resistance	RDS(ON)		40	52	11122	V _G S = 4.5V, I _D = 3.9A	
Diode Forward Voltage	V _{SD}		0.7	1.1	V	V _{GS} = 0V, I _S = 1.25A	
DYNAMIC CHARACTERISTICS (Note 8)	•			•	•		
Input Capacitance	Ciss	_	574	_		.,	
Output Capacitance	Coss	_	87.8	_	pF	$V_{DS} = 20V$, $V_{GS} = 0V$, $f = 1MHz$	
Reverse Transfer Capacitance	C _{rss}	_	38.7	_			
Gate Resistance	Rg	_	1.6	_	Ω V _{DS} = 0V, V _{GS} = 0V, f = 1M		
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	5.9	_			
Total Gate Charge (V _{GS} = 10V)	Qg		12.5	_	nC	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Gate-Source Charge	Qgs		1.7	_	nc nc	$V_{DS} = 20V, I_{D} = 3.9A$	
Gate-Drain Charge	Qgd		2.2	_			
Turn-On Delay Time	t _{D(ON)}		3.1	_			
Turn-On Rise Time	t _R		2.6	_		V _{DD} = 20V, V _{GS} = 10V,	
Turn-Off Delay Time	t _{D(OFF)}	_	15	_	ns	$R_L = 20\Omega$, $R_G = 6\Omega$	
Turn-Off Fall Time	t _F	_	5.5	_	1		
Reverse Recovery Time	t _{RR}	_	6.5	_	ns	1 0 00 11/14 5000/	
Reverse Recovery Charge	Q _{RR}	_	1.2	_	nC	$I_F = 3.9A, di/dt = 500A/\mu s$	

Notes:

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.



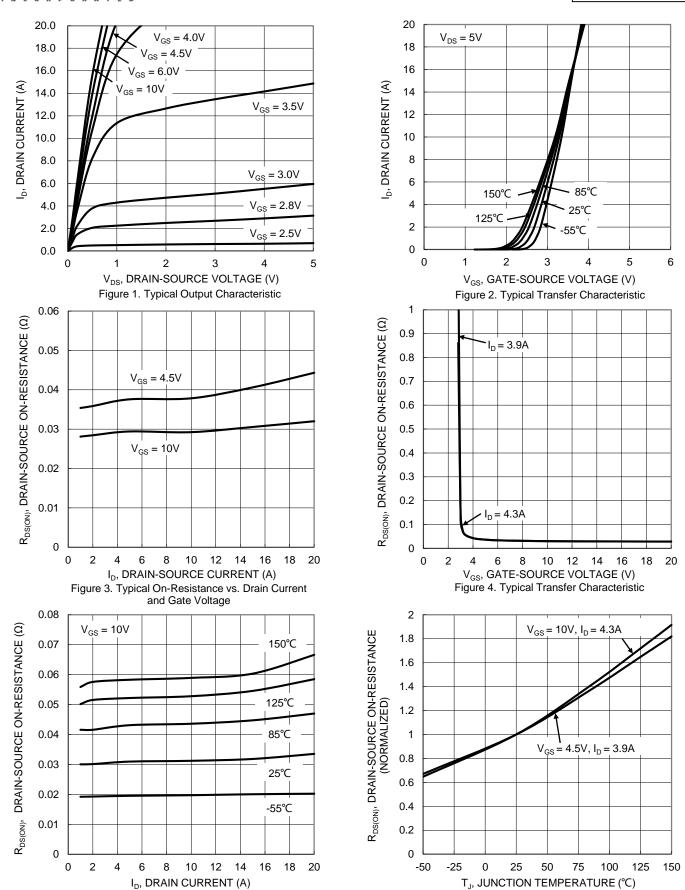


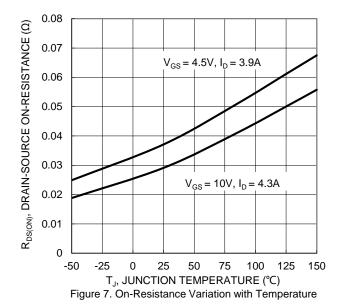
Figure 5. Typical On-Resistance vs. Drain Current

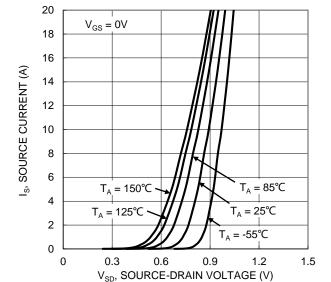
and Temperature

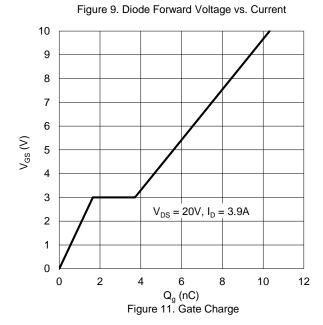
Figure 6. On-Resistance Variation with Temperature











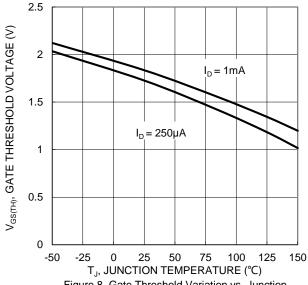


Figure 8. Gate Threshold Variation vs. Junction Temperature

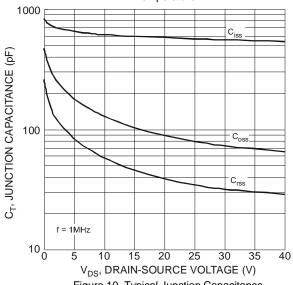
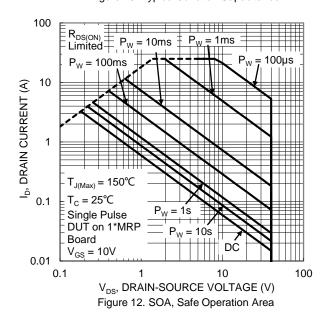


Figure 10. Typical Junction Capacitance





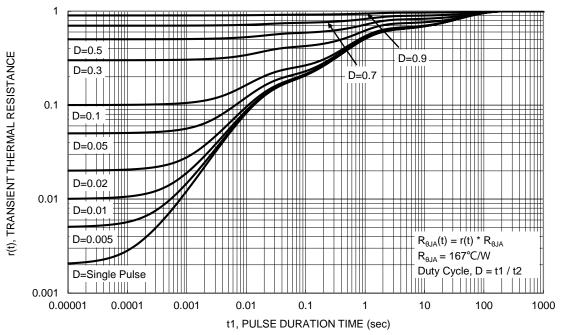


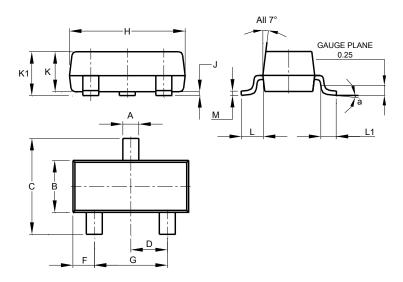
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

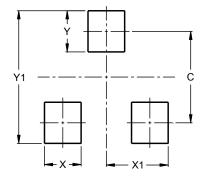


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	a 0° 8°					
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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